

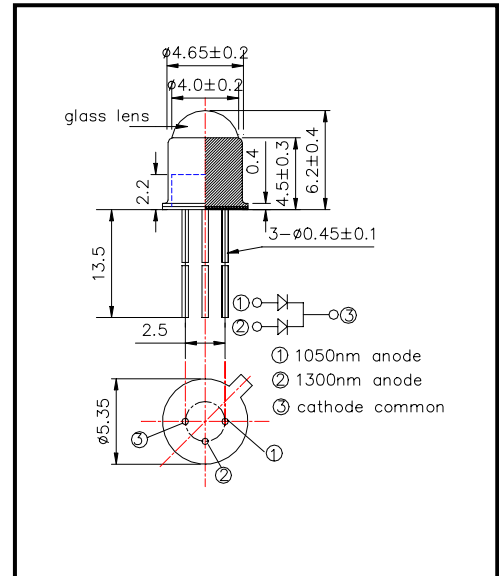
# L1050/1300-35D32 multi-wavelength LED

L1050/1300-35D32 consists of an InGaAsP LEDs , LED mounted on TO-18 stem with a glass ball lens. On forward bias it emits a spectral band of radiation, which peak at 1050nm and 1300nm without sub-peak.

◆ Specifications

- 1) Product Name            Multi-wavelength LED Lamp
- 2) Type No.                L1050/1300-35D32
- 3) Chip
- (1) Chip material        InGaAsP
- (2) Chip dimension     400um
- (3) Peak wavelength    1050nm, 1300nm
- 4) Package
- (1) Stem                    TO-18 3pins type
- (2) Lens                    Φ5mm glass ball lens

◆ Outer dimension(Unit: mm)



◆ Absolute Maximum Ratings [Ta=25°C]

Item	Symbol	Maximum Rated Value		Unit
		850	850	
Power Dissipation	P <sub>D</sub>	130	130	mW
Forward Current	I <sub>F</sub>	100	100	mA
Pulse Forward Current	I <sub>F</sub>	1000	1000	mA
Reverse Voltage	V <sub>R</sub>	5		V
Operating Temperature	T <sub>OPR</sub>	-40 ~ +80		°C
Storage Temperature	T <sub>STG</sub>	-40 ~ +100		°C
Soldering Temperature	T <sub>SOL</sub>	265		°C

‡Soldering condition: Soldering condition must be completed within 3 seconds at 265°C and is allowed in the area apart 3mm from the bottom of the lamp.

◆ Electro-Optical Characteristics [Ta=25°C]

Symbol	Wavelength	Condition	Minimum	Typical	Maximum	Unit
V <sub>F</sub>	1050	I <sub>F</sub> =50mA		1.1	1.3	V
	1300			1.1	1.3	
I <sub>R</sub>	1050/1300	V <sub>R</sub> =5V			10	uA
P <sub>O</sub>	1050	I <sub>F</sub> =50mA		4.0		mW
	1300			4.0		
I <sub>E</sub>	1050	I <sub>F</sub> =50mA		-		mW/sr
	1300			-		
λ <sub>P</sub>	1050	I <sub>F</sub> =50mA	1000	1050	1100	nm
	1300		1250	1300	1350	
Δλ	1050	I <sub>F</sub> =50mA		80		nm
	1300			80		

‡Radiated Power is measured by G8370-85.

‡Radiant Intensity is measured by Tektronix J-6512.